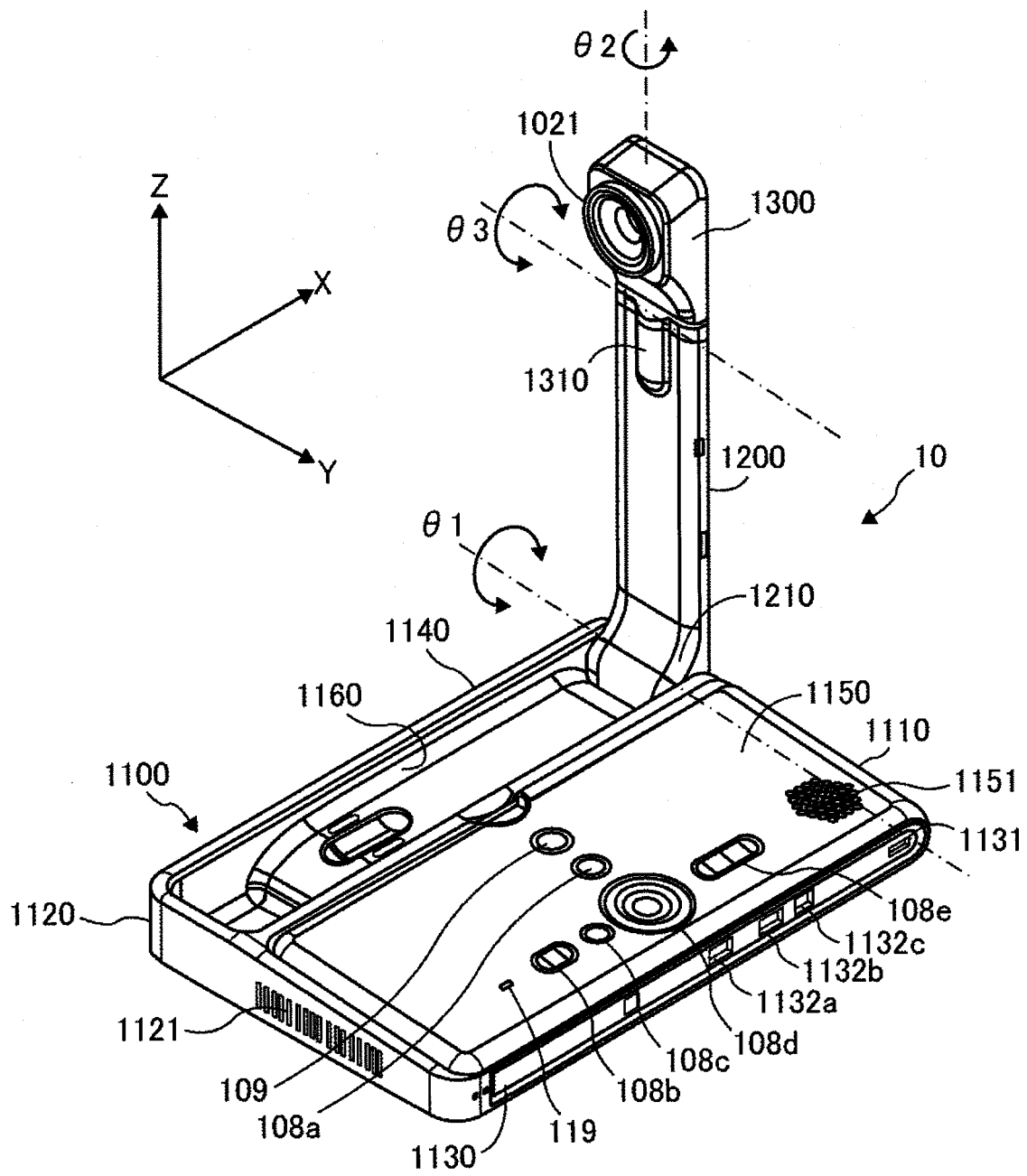
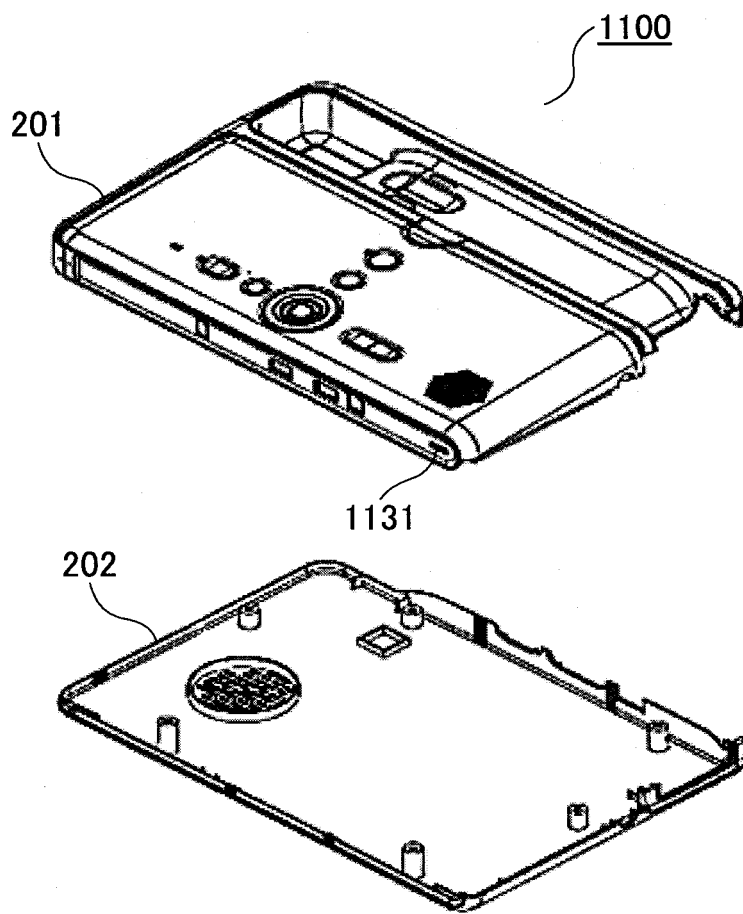


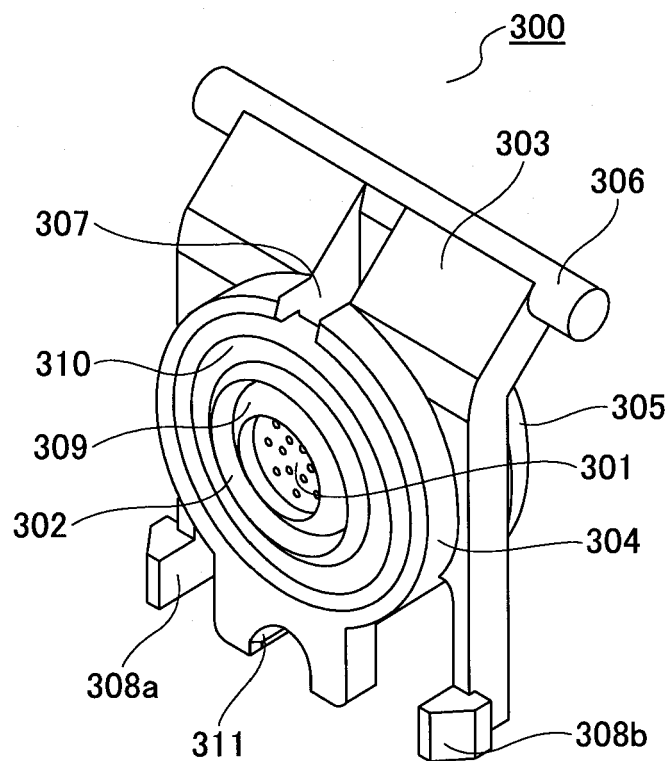
[図1]



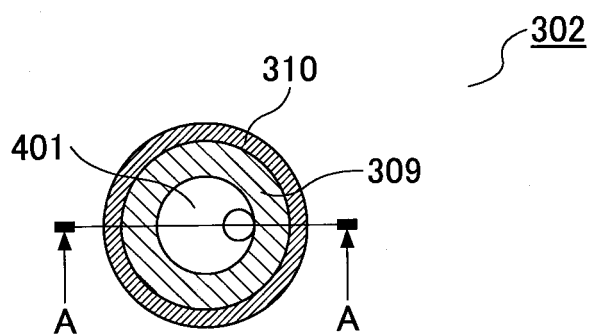
[図2]



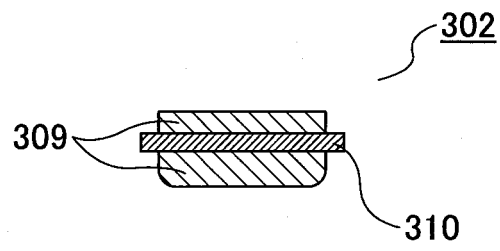
[図3]



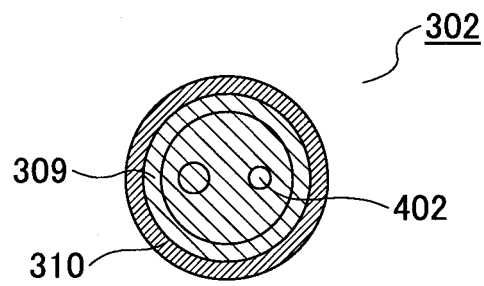
[図4A]



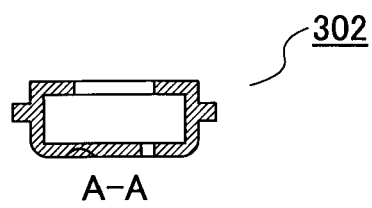
[図4B]



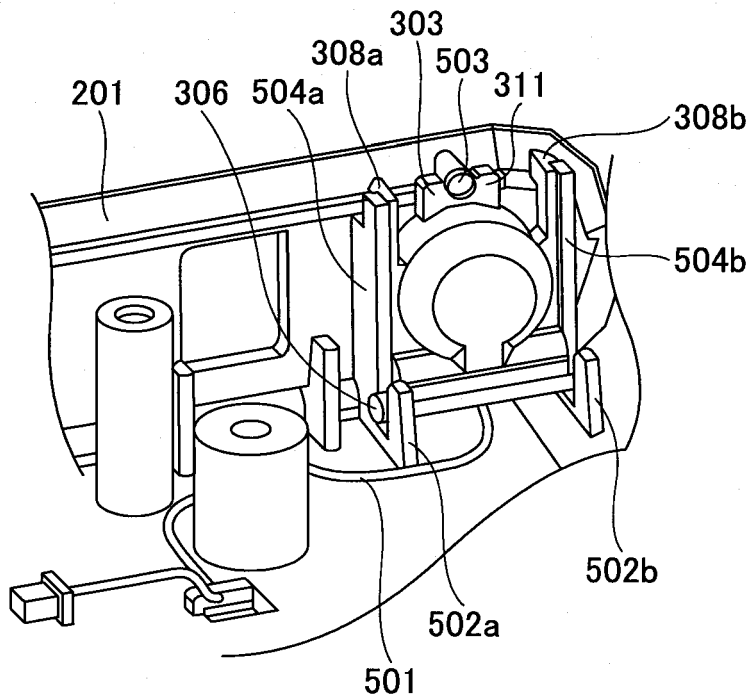
[図4C]



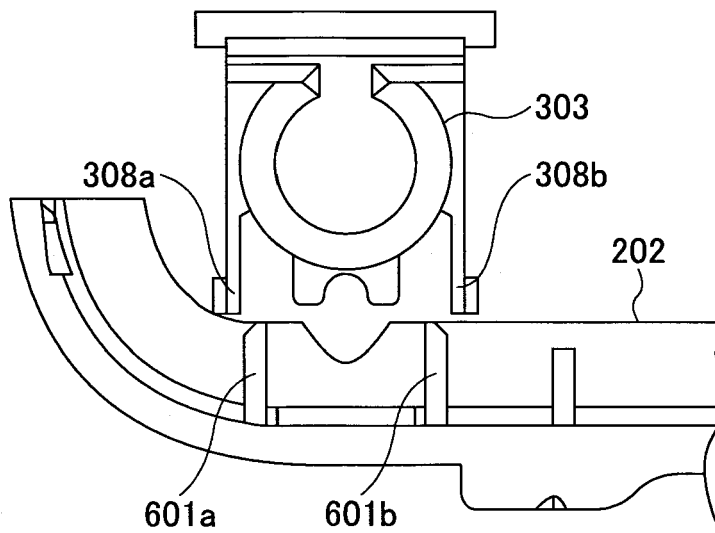
[図4D]



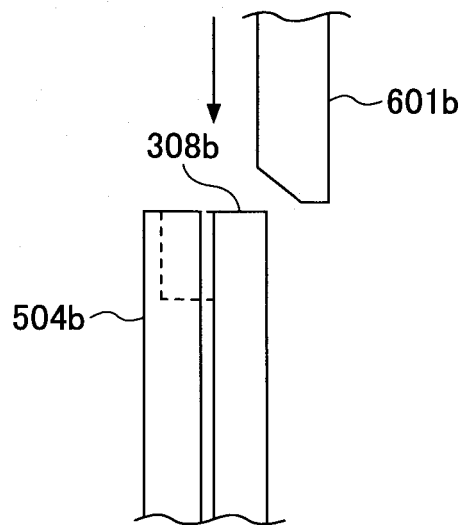
[図5]



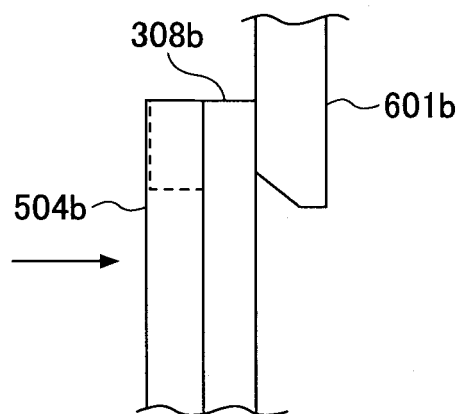
[図6]



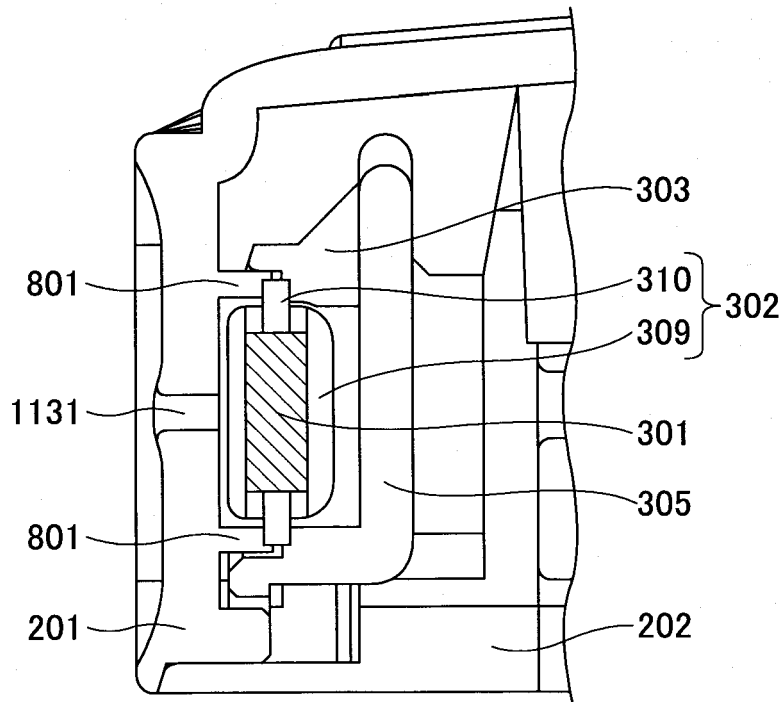
[図7A]



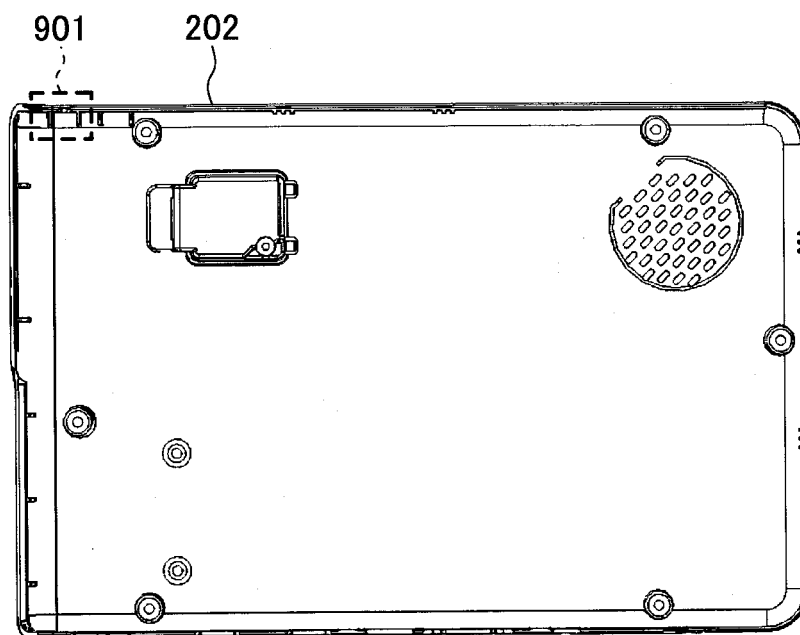
[図7B]



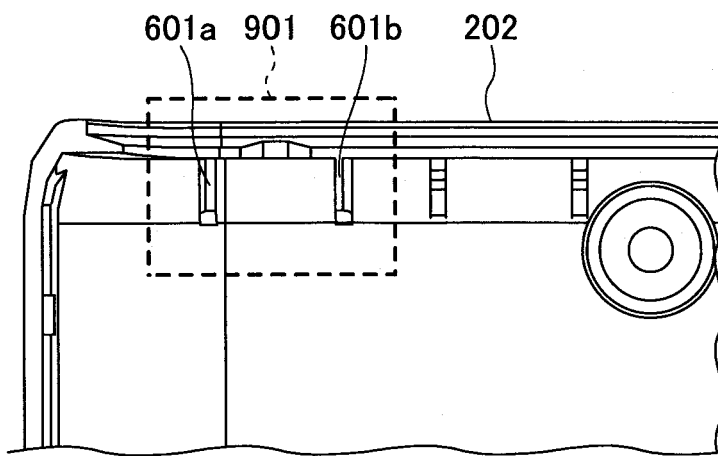
[図8]



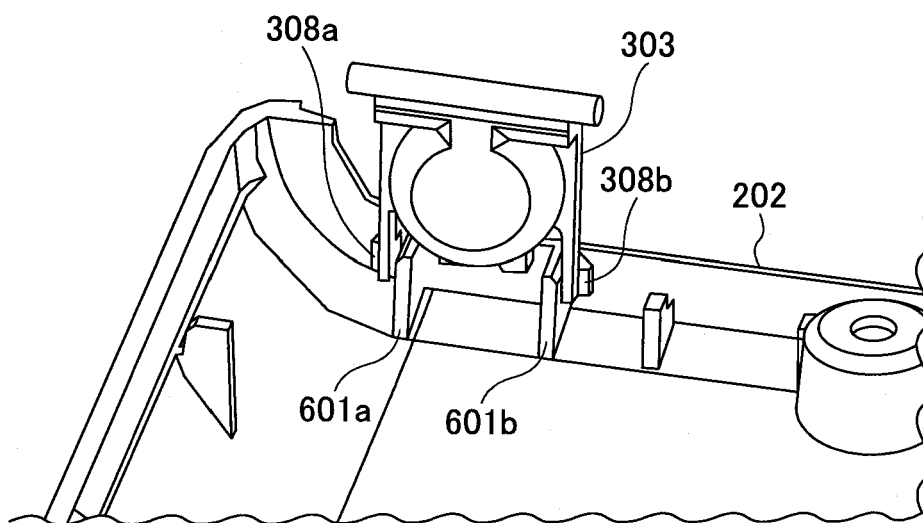
[図9]



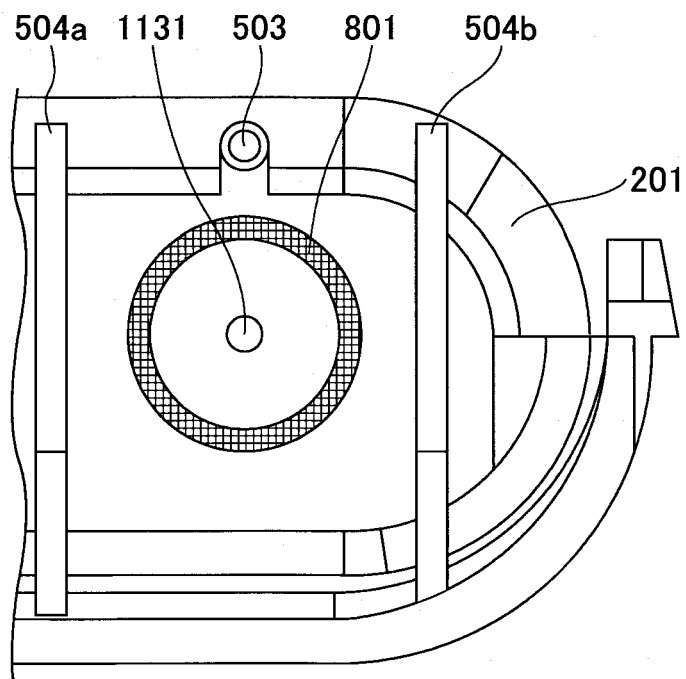
[図10]



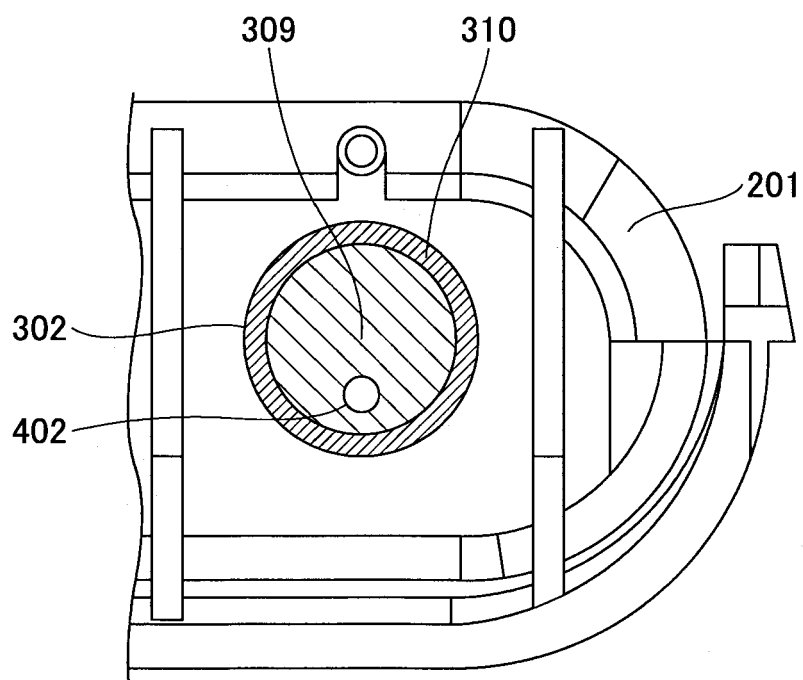
[図11]



[図12]

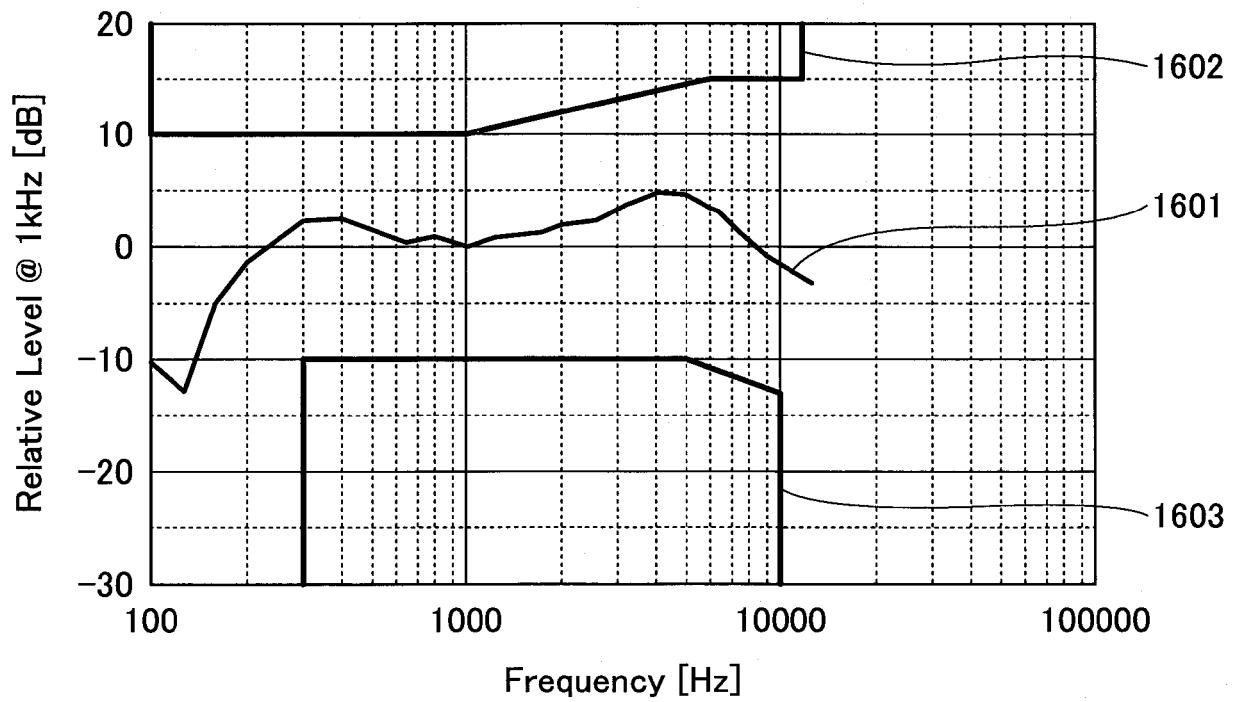


[図13]

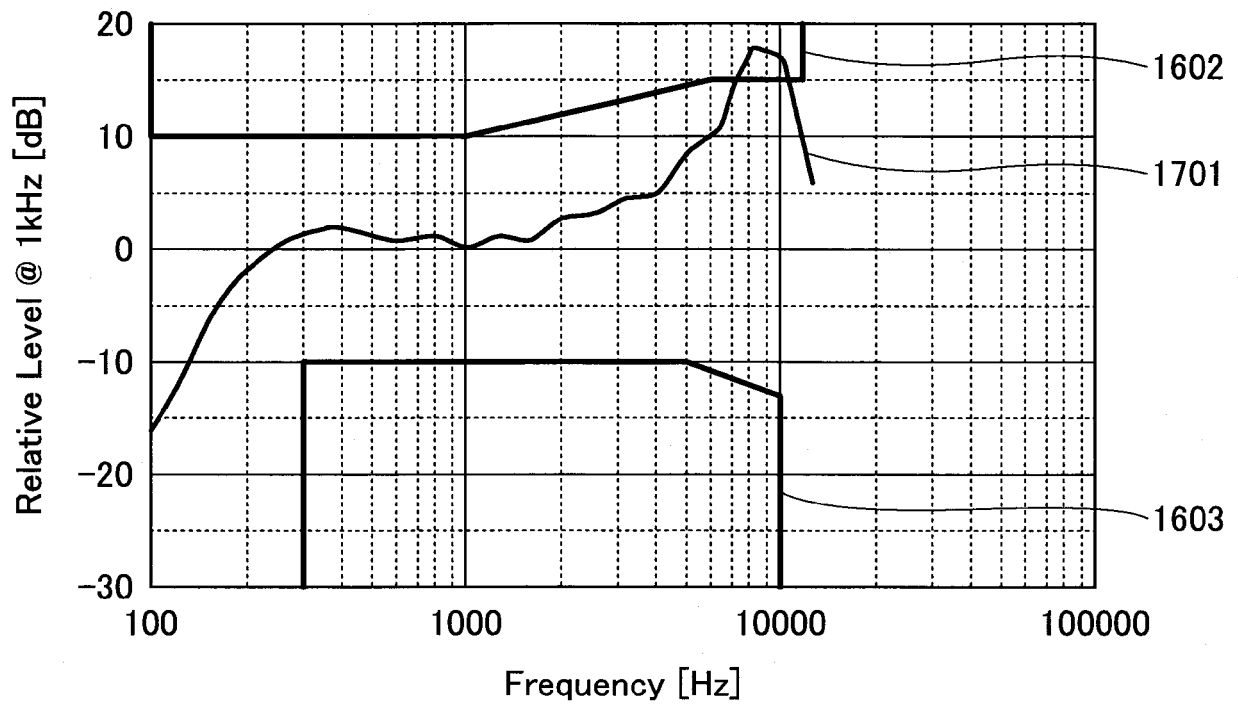


A cross-sectional view of a device structure 201. The structure consists of a base layer 201 with a grid pattern. On top of the base layer is a layer 801 with a grid pattern. Above layer 801 is a layer 310 with a diagonal hatching pattern. On top of layer 310 is a layer 309 with a diagonal hatching pattern. The top surface of layer 309 is rounded, with a label 302 pointing to the rounded edge. A dimension line indicates the height of layer 801 is h .

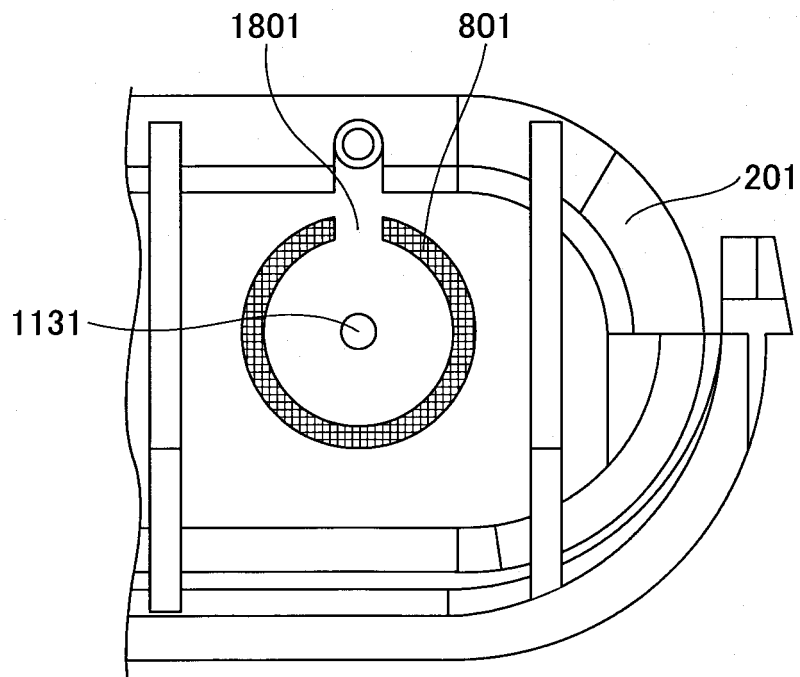
[図16]



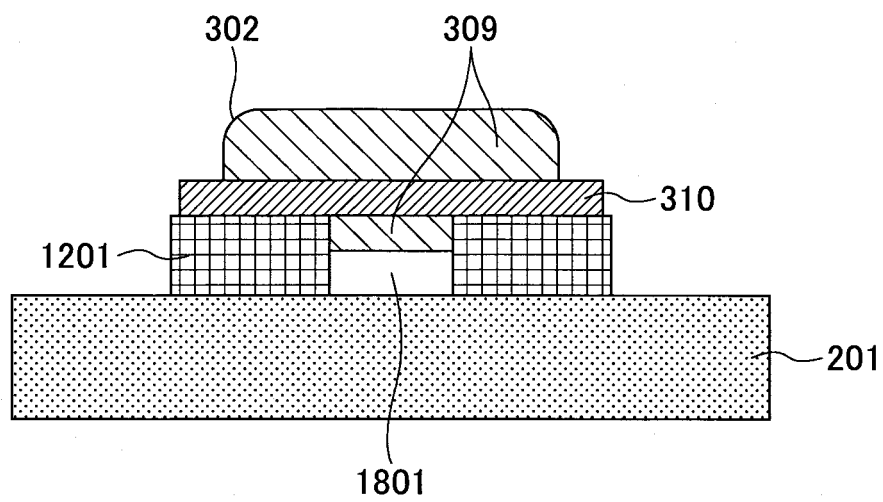
[図17]



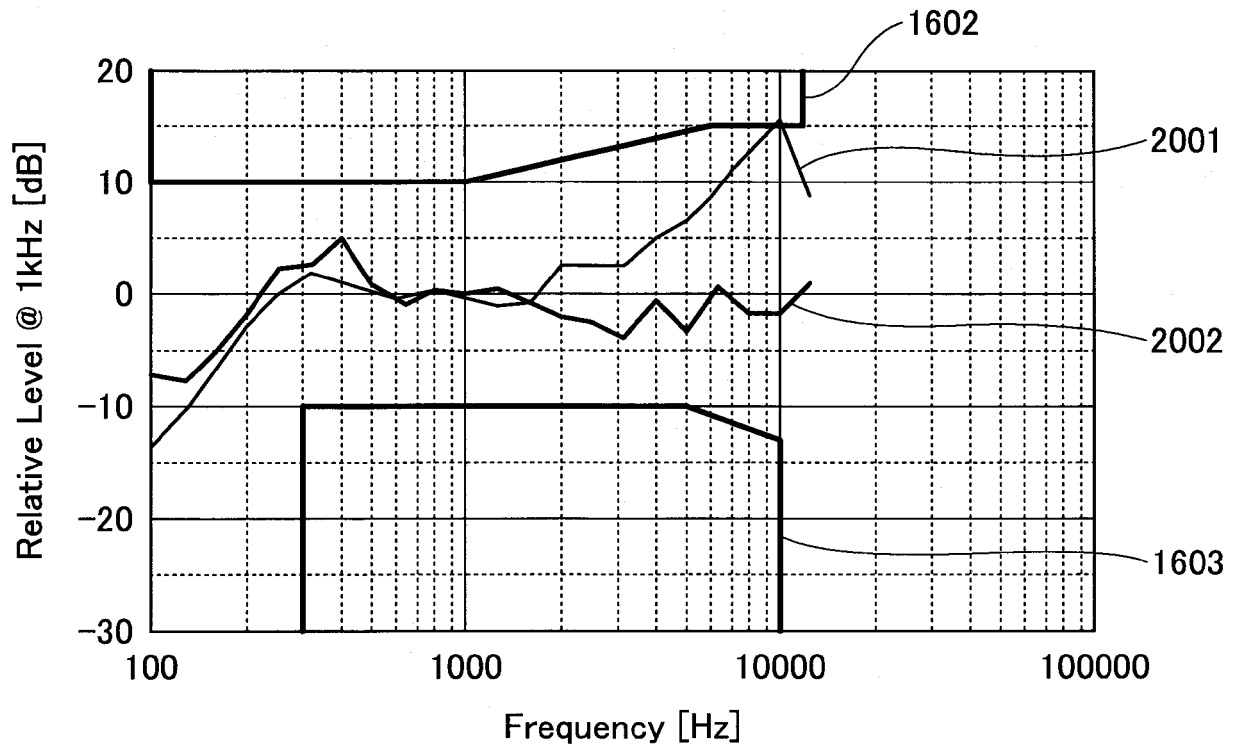
[図18]



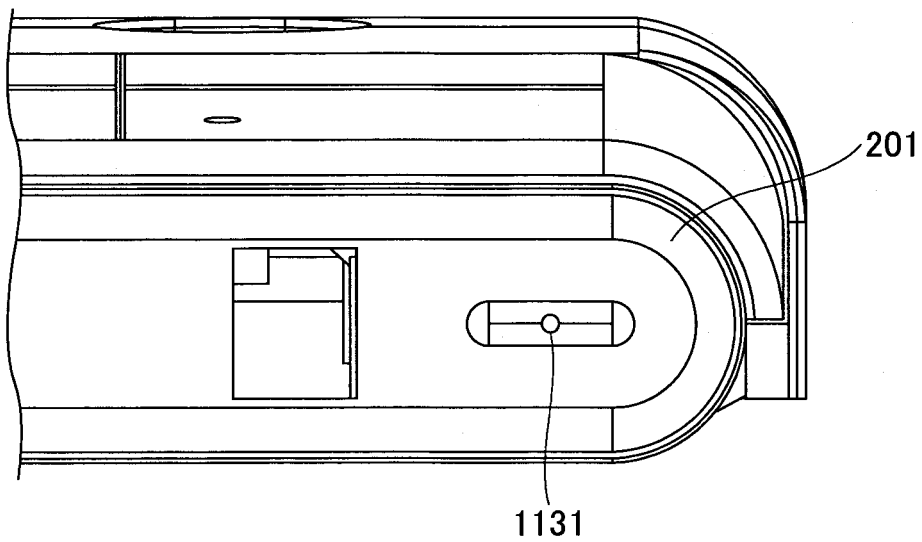
[図19]



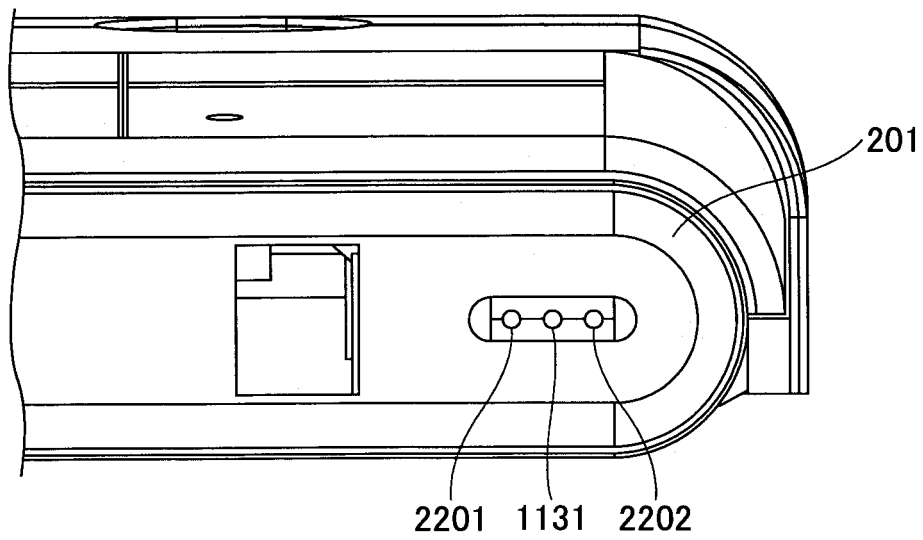
[図20]



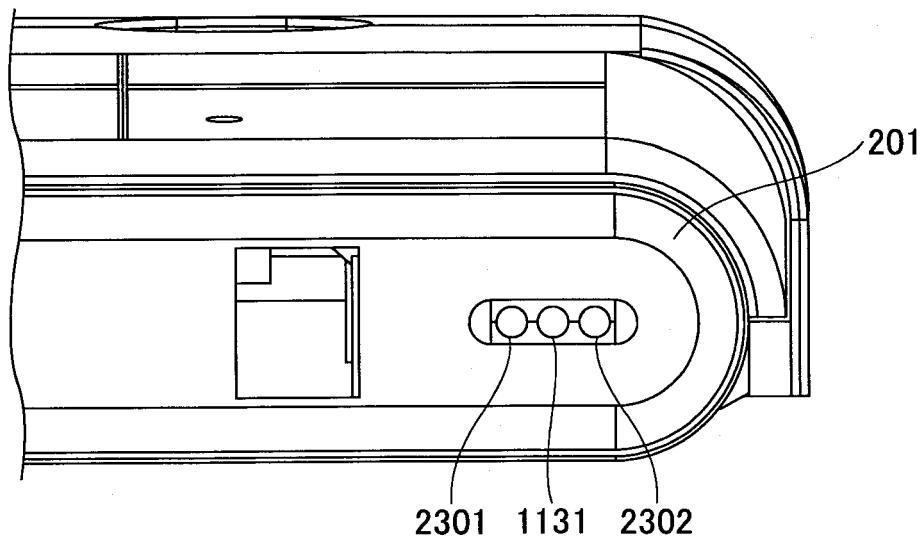
[図21]



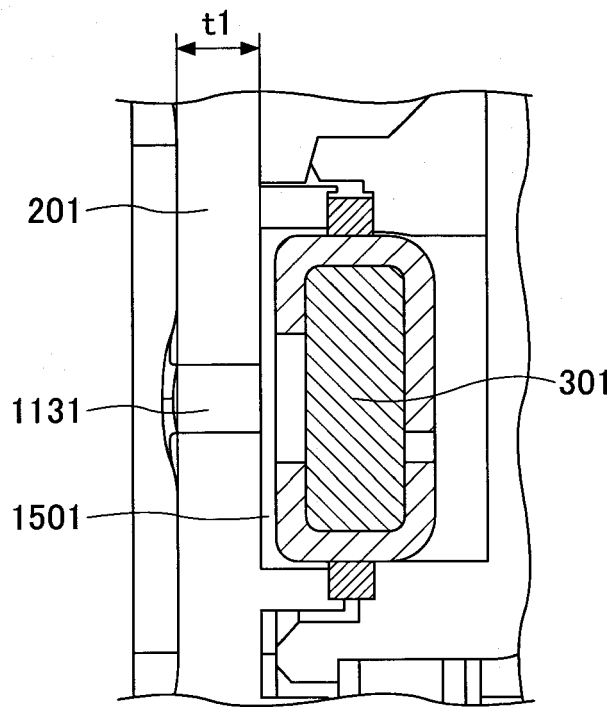
[図22]



[図23]



[図24A]



[図24B]

